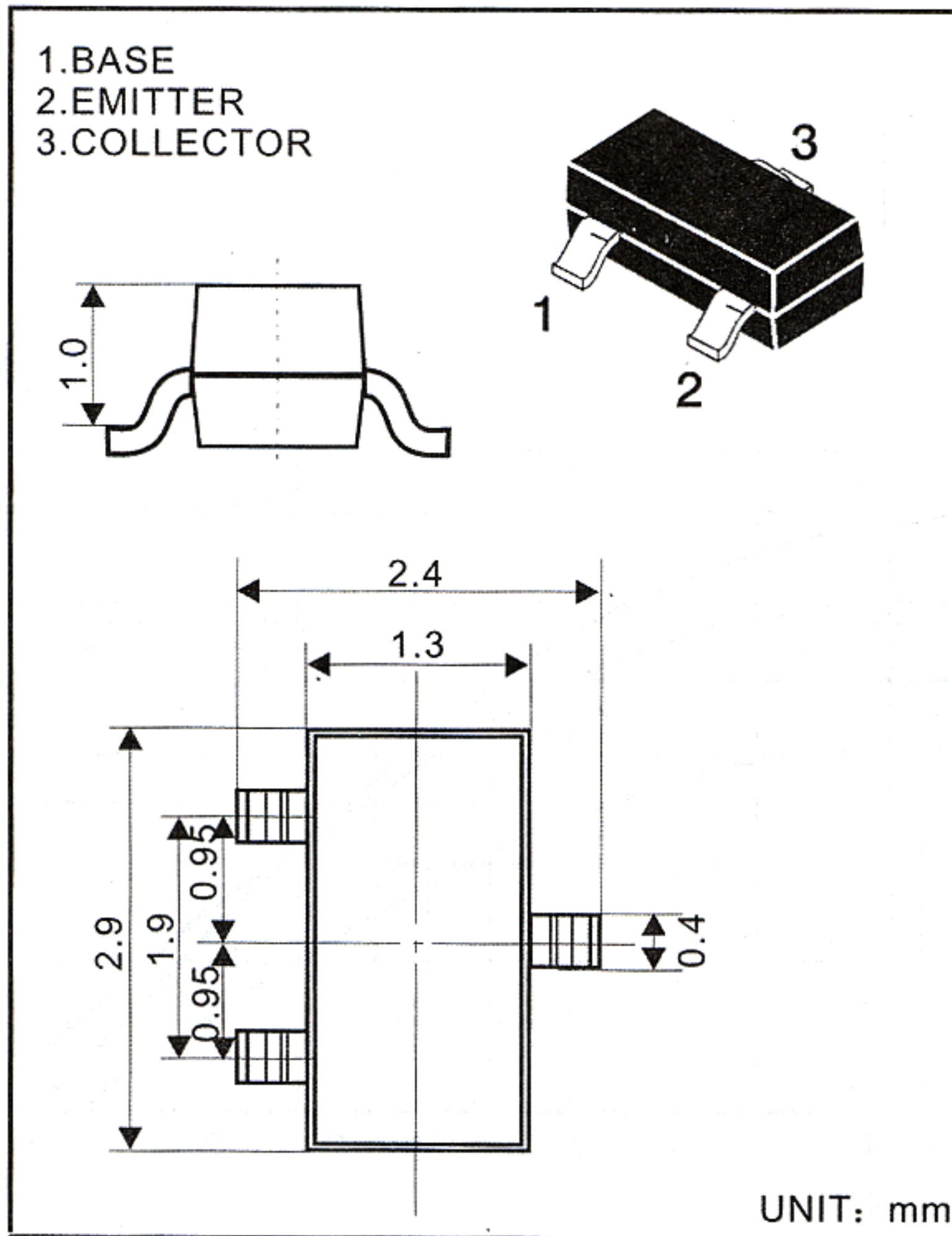


## MMBT3904LT1 TRANSISTOR (NPN)



### FEATURES

#### Power dissipation

$P_{CM}$ : 0.2 W ( $T_{amb}=25^{\circ}C$ )

#### Collector current

$I_{CM}$ : 0.2 A

#### Collector-base voltage

$V_{(BR)CBO}$ : 60V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

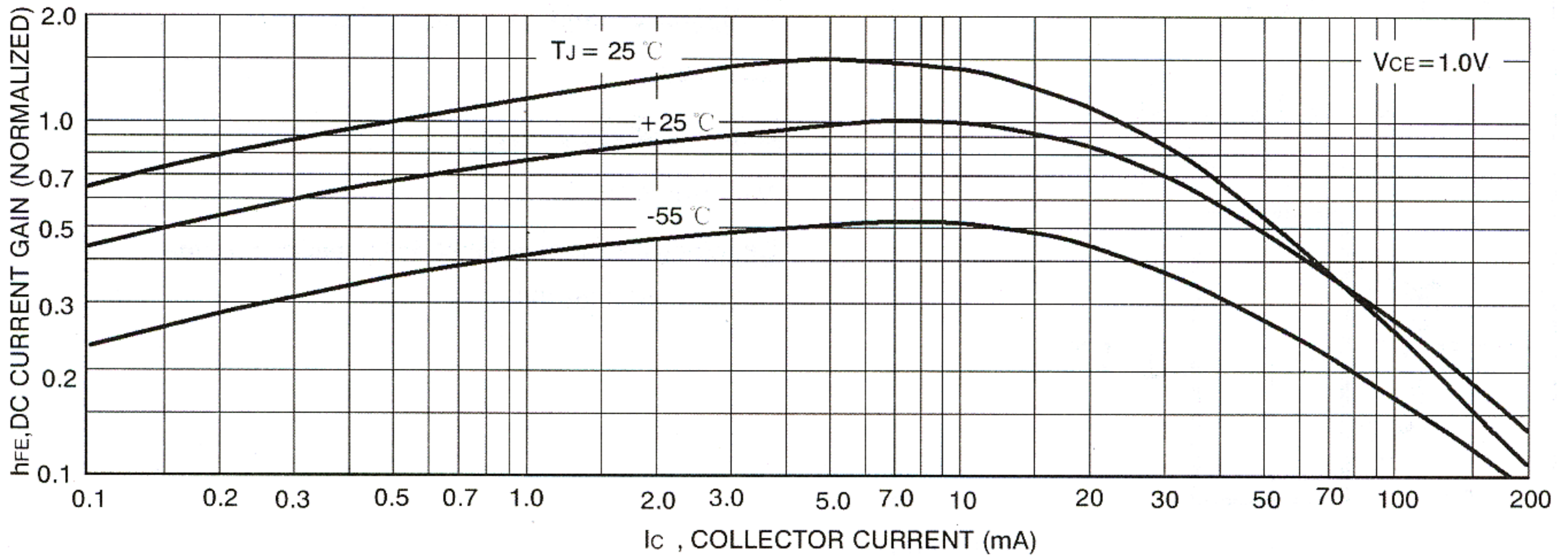
### ELECTRICAL CHARACTERISTICS

( $T_{amp}=25^{\circ}C$  unless otherwise specified)

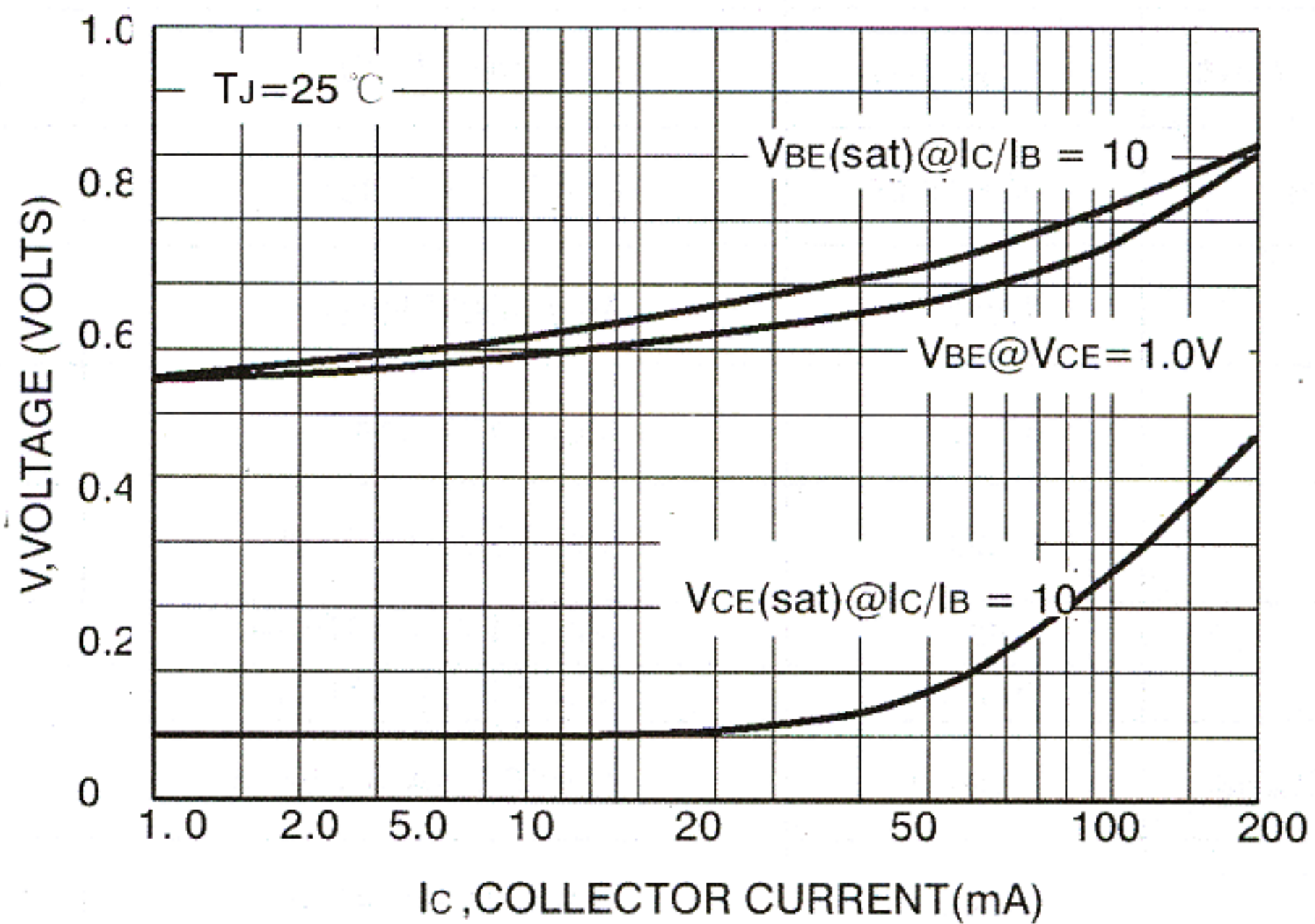
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_C=100\mu A, I_B=0$	6		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$		0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=40V, I_B=0$		0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0mA$		0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=10mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=50mA$	60		
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C=100mA, I_B=5mA$		0.4	V
Base-emitter saturation voltage	$V_{BEsat}$	$I_C=50mA, I_B=5mA$		0.95	
Transition frequency	$f_T$	$V_{CE}=20V, I_C=10mA, f=100MHz$	250		MHz

DEVICE MARKING : MMBT3904LT1=1AM





DC Current Gain



"On" Voltages